



## 2.4 GHz High-Power and High-Gain Power Amplifier SST12LP15A

Data Sheet

### FUNCTIONAL BLOCKS

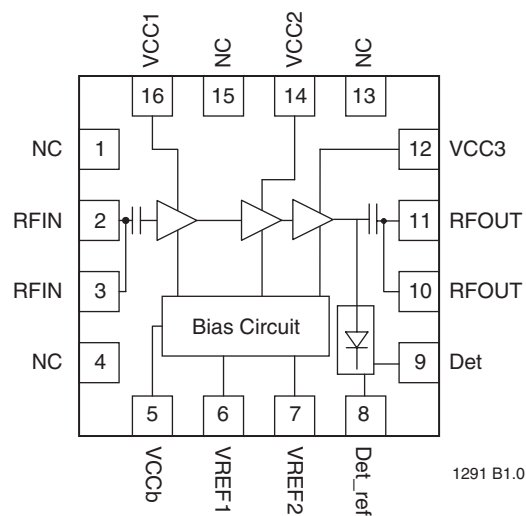


FIGURE 1: Functional Block Diagram6

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### PIN ASSIGNMENTS

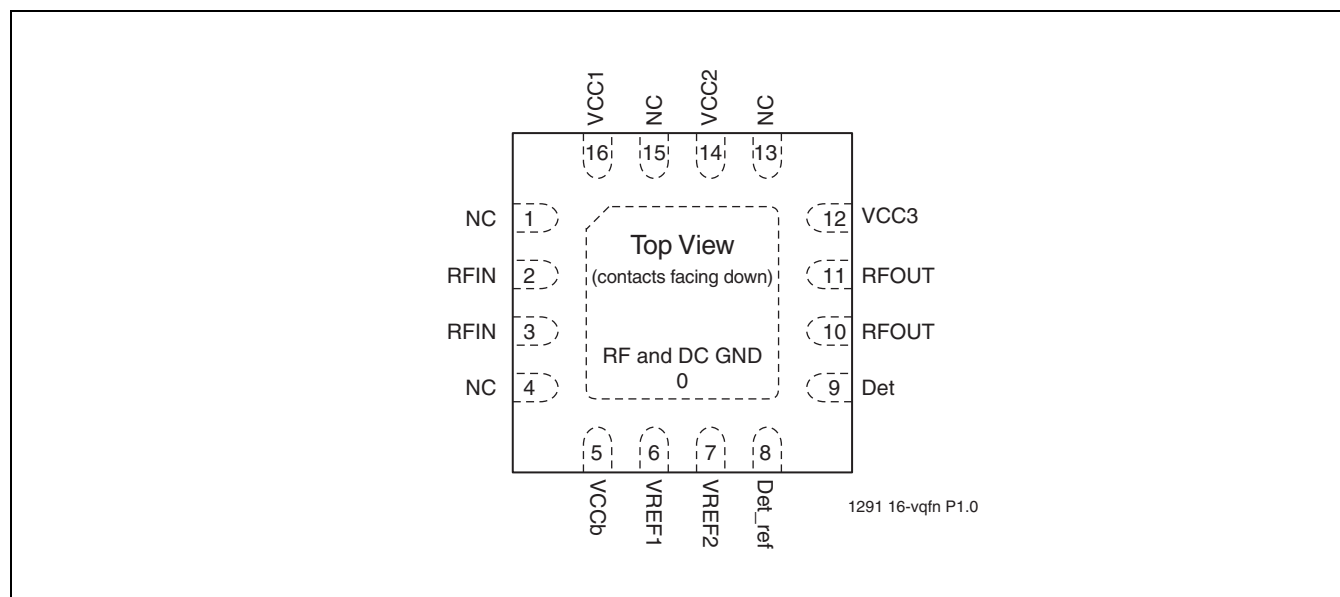


FIGURE 2: Pin Assignments for 16-contact VQFN

### PIN DESCRIPTIONS

TABLE 1: Pin Description

Symbol	Pin No.	Pin Name	Type <sup>1</sup>	Function
GND	0	Ground		The center pad should be connected to RF ground with several low inductance, low resistance vias.
NC	1	No Connection		Unconnected pins.
RFIN	2		I	RF input, DC decoupled
RFIN	3		I	RF input, DC decoupled
NC	4	No Connection		Unconnected pins.
VCCb	5	Power Supply	PWR	Supply voltage for bias circuit
VREF1	6		PWR	1st and 2nd stage idle current control
VREF2	7		PWR	3rd stage idle current control
Det_ref	8		O	On-chip power detector reference
Det	9		O	On-chip power detector
RFOUT	10		O	RF output
RFOUT	11		O	RF output
VCC3	12	Power Supply	PWR	Power supply, 3rd stage
NC	13	No Connection		Unconnected pins.
VCC2	14	Power Supply	PWR	Power supply, 2nd stage
NC	15	No Connection		Unconnected pins.
VCC1	16	Power Supply	PWR	Power supply, 1st stage

1. I=Input, O=Output

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### ELECTRICAL SPECIFICATIONS

The AC and DC specifications for the power amplifier interface signals. Refer to Table 2 for the DC voltage and current specifications. Refer to Figures 3 through 10 for the RF performance.

**Absolute Maximum Stress Ratings** (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Input power to pins 2 and 3 ( $P_{IN}$ ) ..... +5 dBm  
 Average output power ( $P_{OUT}$ )<sup>1</sup> ..... +28 dBm  
 Supply Voltage at pins 5, 12, 14, 16 ( $V_{CC}$ ) ..... -0.3V to +4.6V  
 Reference voltage to pins 6 ( $V_{REF1}$ ) and pin 7 ( $V_{REF2}$ ) ..... -0.3V to +3.6V  
 DC supply current ( $I_{CC}$ ) ..... 500 mA  
 Operating Temperature ( $T_A$ ) ..... -40°C to +85°C  
 Storage Temperature ( $T_{STG}$ ) ..... -40°C to +120°C  
 Maximum Junction Temperature ( $T_J$ ) ..... +150°C  
 Surface Mount Solder Reflow Temperature ..... 260°C for 10 seconds

1. Never measure with CW source. Pulsed single-tone source with <50% duty cycle is recommended. Exceeding the maximum rating of average output power could cause permanent damage to the device.

### Operating Range

Range	Ambient Temp	$V_{CC}$
Industrial	-40°C to +85°C	3.3V

**TABLE 2: DC Electrical Characteristics at 25°C**

Symbol	Parameter	Min.	Typ	Max.	Unit
$V_{CC}$	Supply Voltage at pins 5, 12, 14, 16	3.0	3.3	4.2	V
$I_{CC}$	Supply Current				
	for 802.11g, 24 dBm		300		mA
	for 802.11b, 25 dBm		350		mA
$I_{CQ}$	Idle current for 802.11g to meet EVM<4% @ 23dBm		80		mA
$I_{OFF}$	Shut down current		1		μA
$V_{REG1}$	Reference Voltage for 1st and 2nd Stage, with 270Ω resistor	2.85	2.90	2.95	V
$V_{REG2}$	Reference Voltage for 3rd Stage, with 100Ω resistor	2.85	2.90	2.95	V

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**TABLE 3: AC Electrical Characteristics for Configuration at 25°C**

Symbol	Parameter	Min.	Typ	Max.	Unit
F <sub>L-U</sub>	Frequency range in 802.11b/g applications (see Figure 11)	2400		2485	MHz
P <sub>OUT</sub>	Output power @ PIN = -10 dBm 11b signals @ PIN = -10 dBm 11g signals		23 23		dBm dBm
G	Small signal gain	31	32		dB
G <sub>VAR1</sub>	Gain variation over each band (2400-2485 MHz)			±0.5	dB
G <sub>VAR2</sub>	Gain ripple over channel (Gain variation over 20 MHz)		0.2		dB
ACPR	Meet 11b spectrum mask Meet 11g OFDM 54 MBPS spectrum mask	24 24	25 25		dBm dBm
Added EVM	@ 23 dBm output with 11g OFDM 54 MBPS signal		3.5		%
2f, 3f, 4f, 5f	Harmonics at 22 dBm, without trapping capacitors			-40	dBc

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### TYPICAL PERFORMANCE CHARACTERISTICS

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$  Unless otherwise specified.

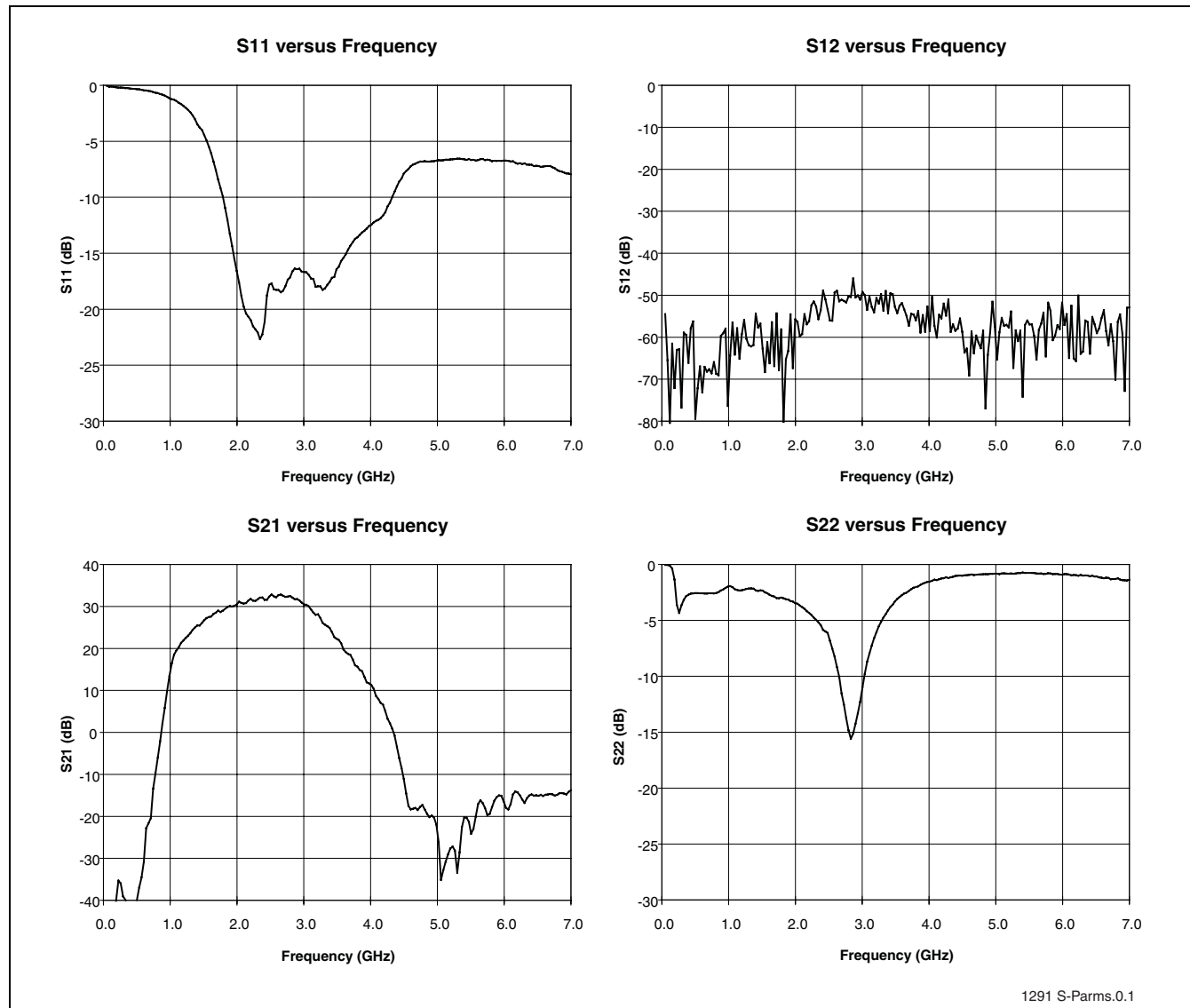


FIGURE 3: S-Parameters

## TYPICAL PERFORMANCE CHARACTERISTICS

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ , 54 Mbps 802.11g OFDM Signal

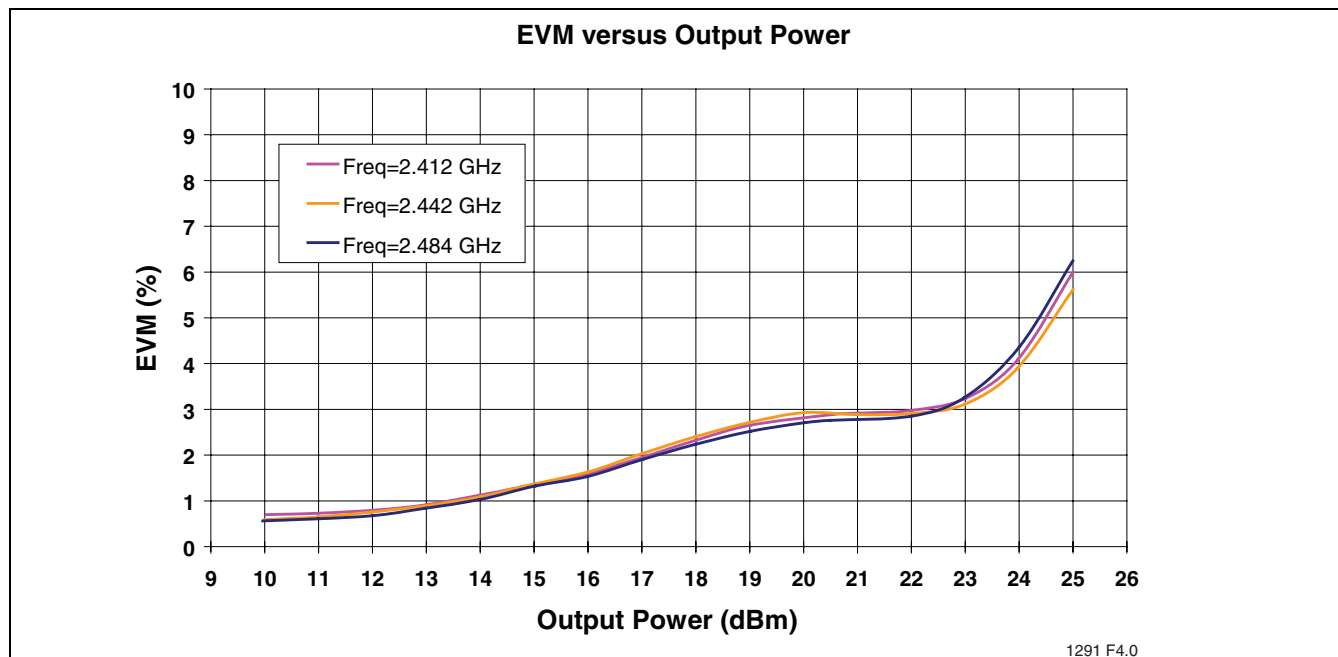


FIGURE 4: EVM versus Output Power

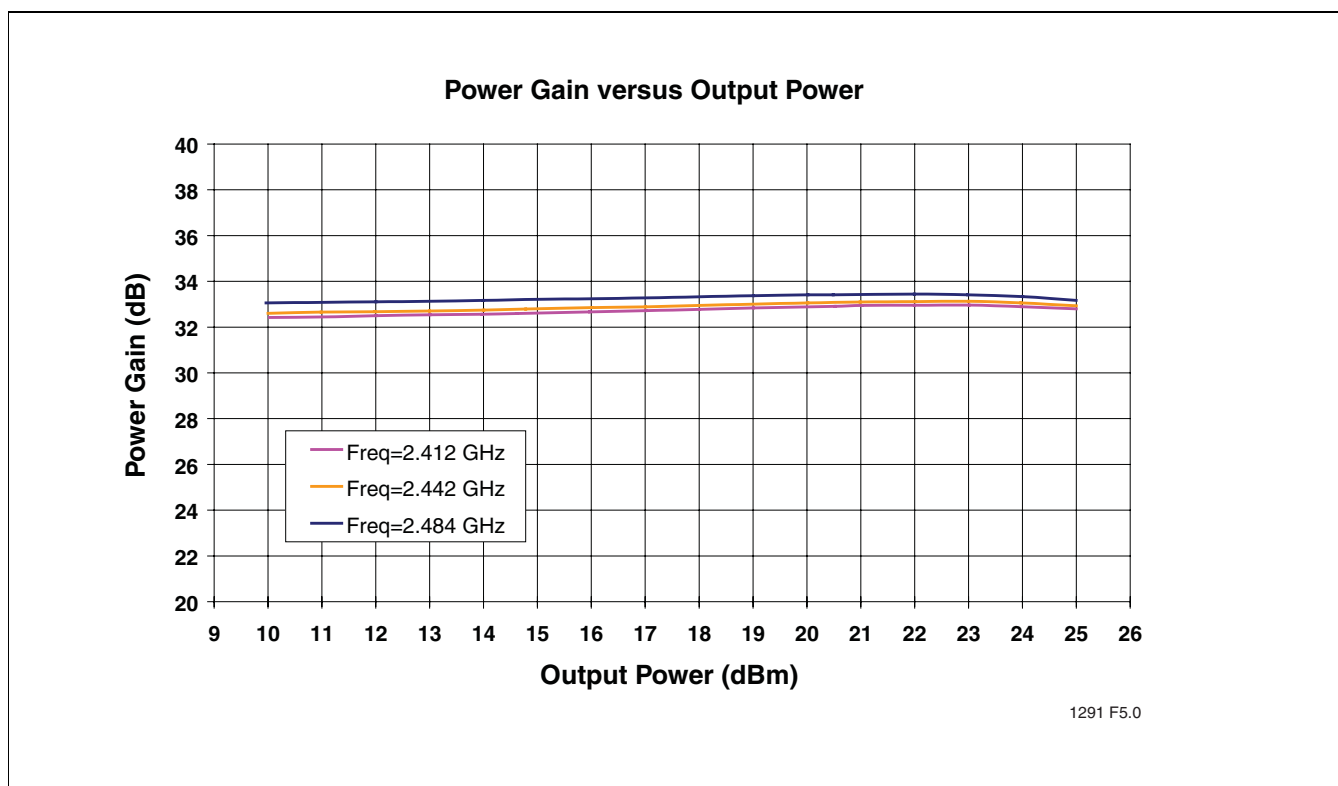
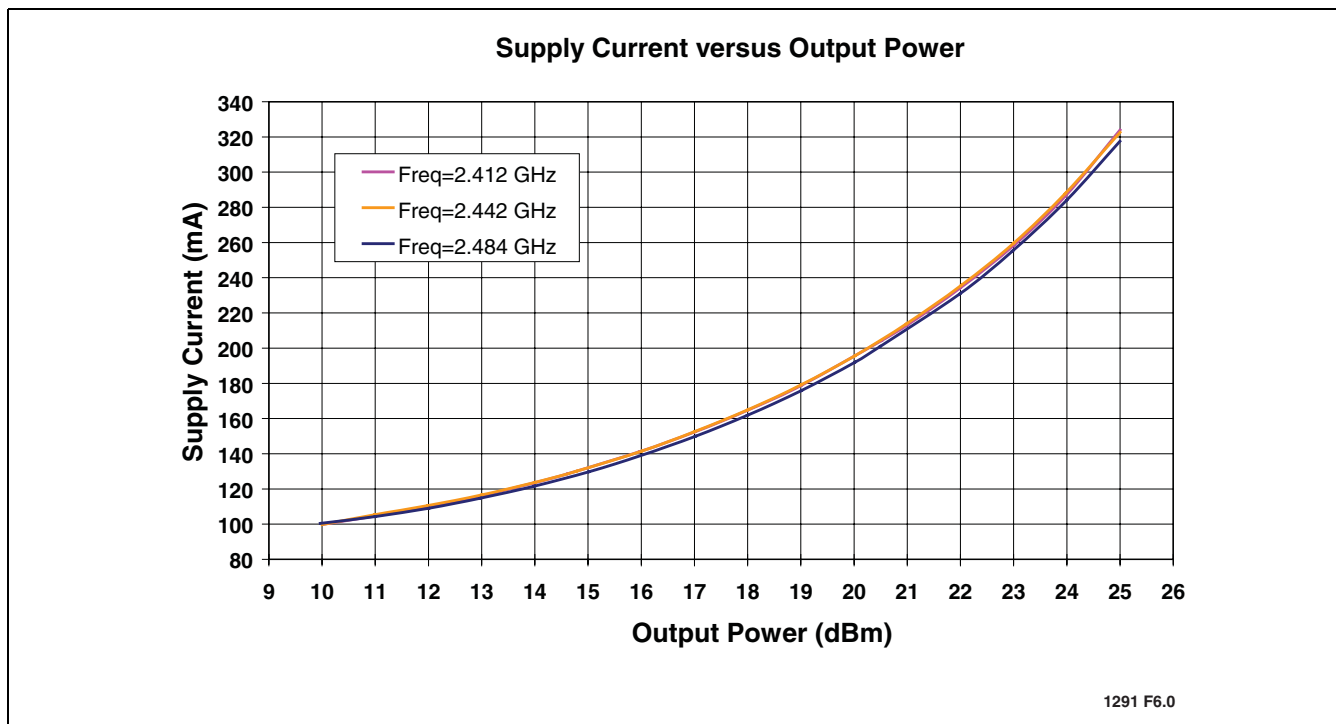


FIGURE 5: Power Gain versus Output Power

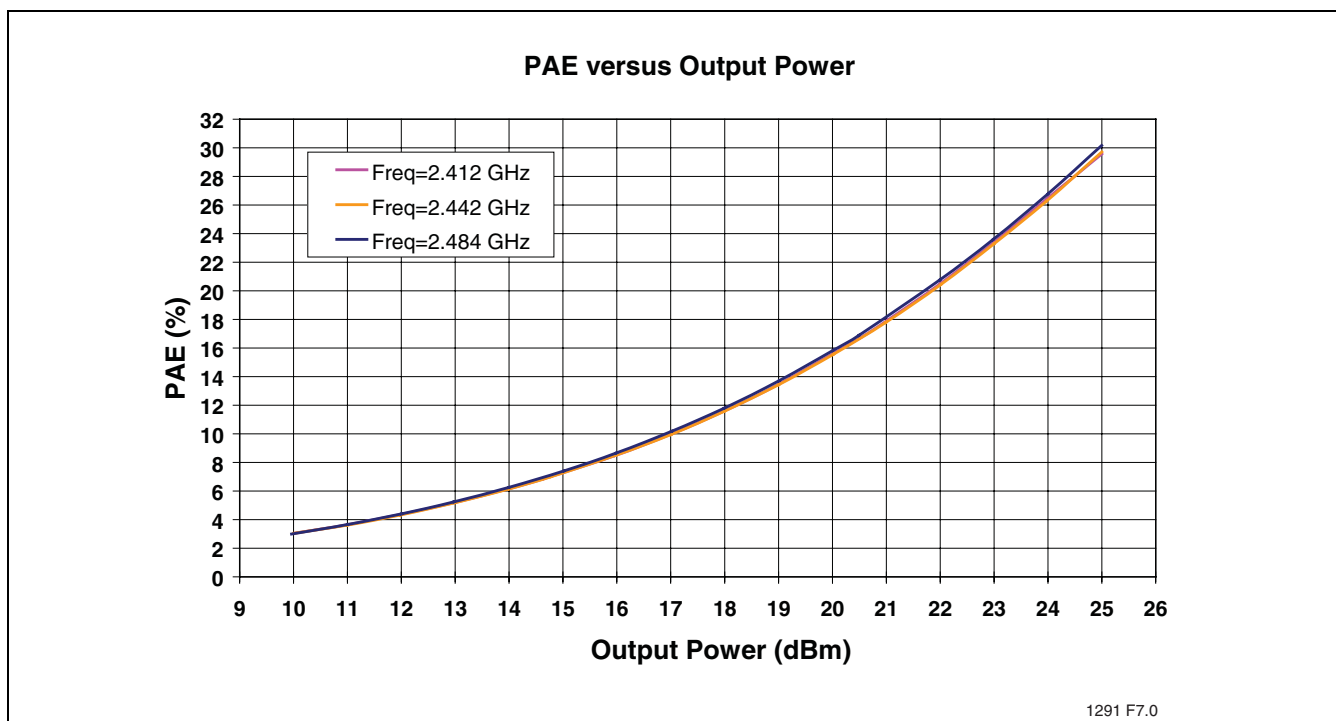


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**FIGURE 6: Total Current Consumption for 802.11g Operation versus Output Power**

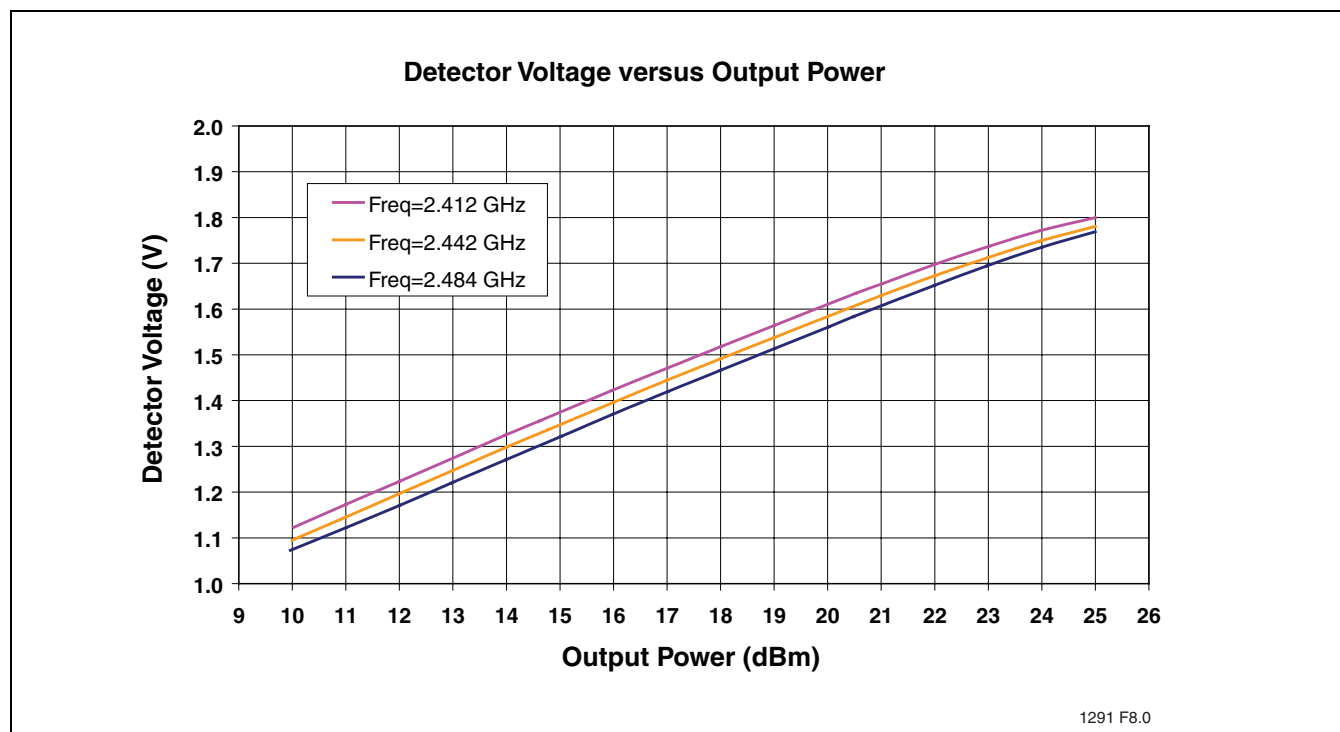


**FIGURE 7: PAE versus Output Power**

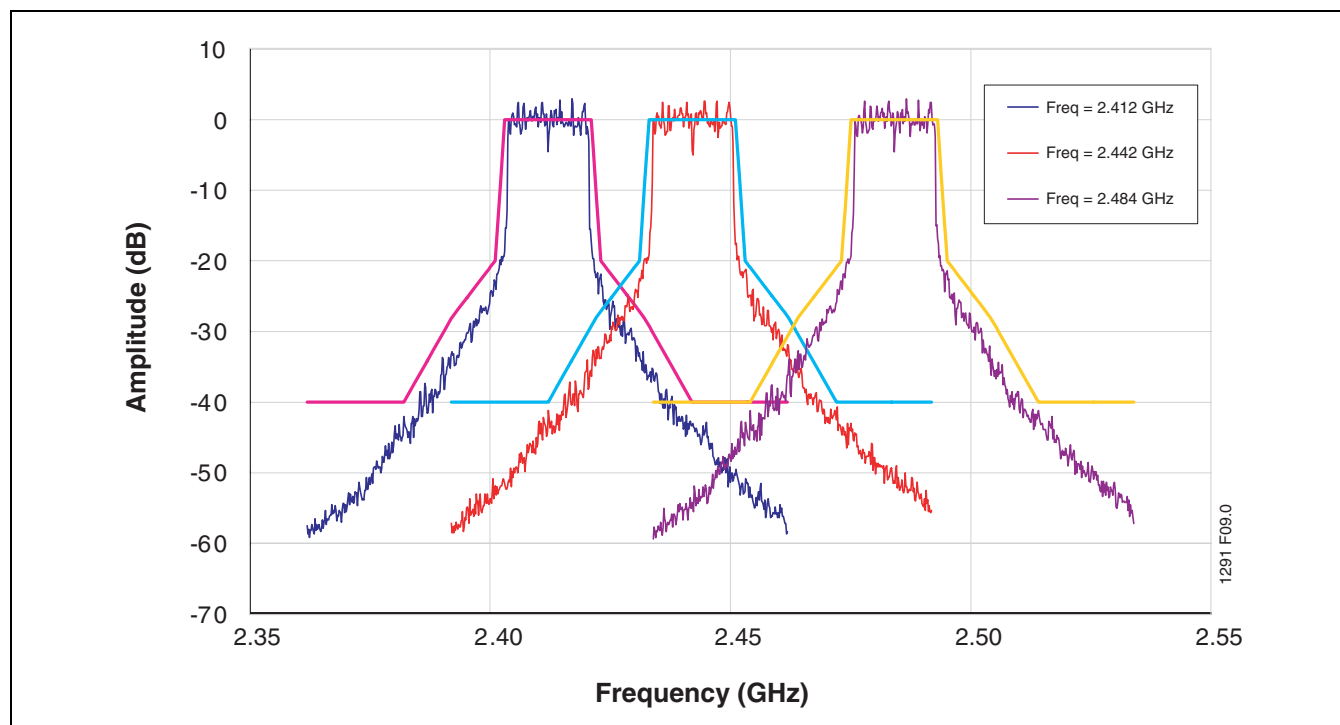
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**FIGURE 8: Detector Characteristic versus Output Power**



**FIGURE 9: 802.11g Spectrum Mask at 24 dBm, Total current 300 mA**





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### TYPICAL PERFORMANCE CHARACTERISTICS

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ , 1 Mbps 802.11b CCK signal

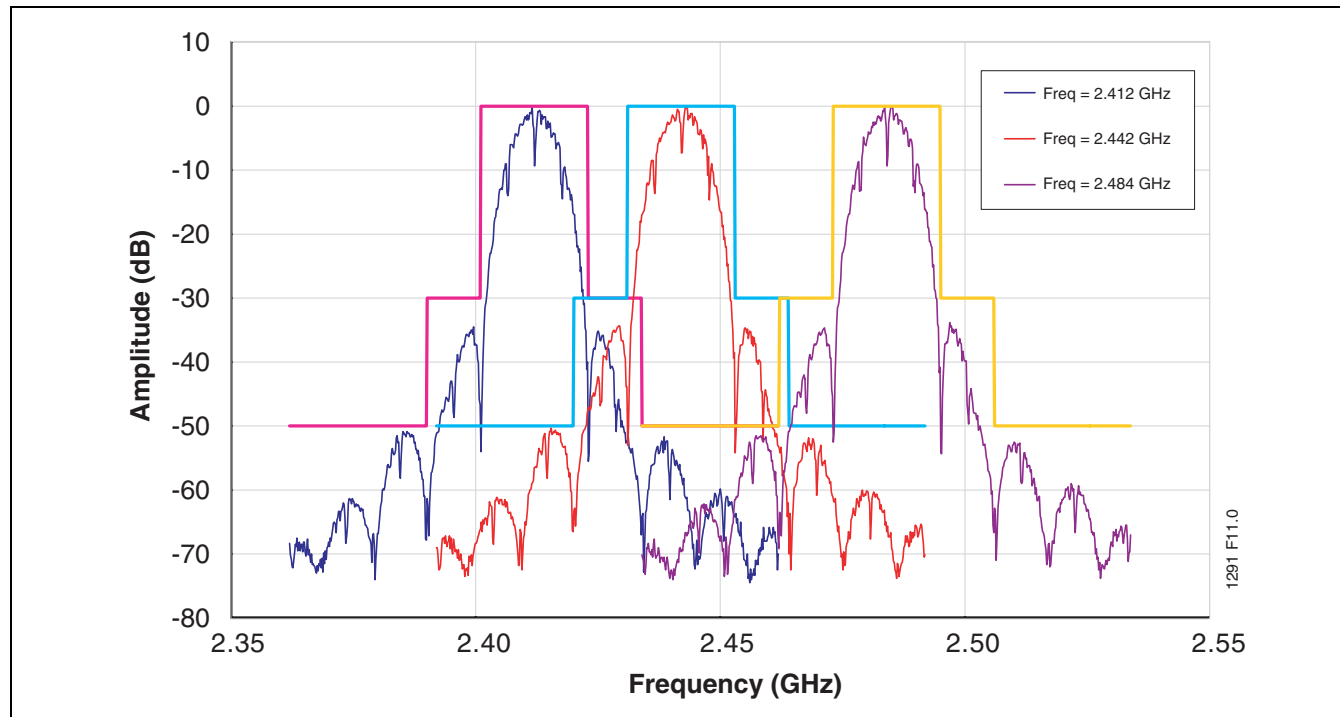


FIGURE 10: 802.11b Spectrum Mask at 25 dBm, Total current 350 mA

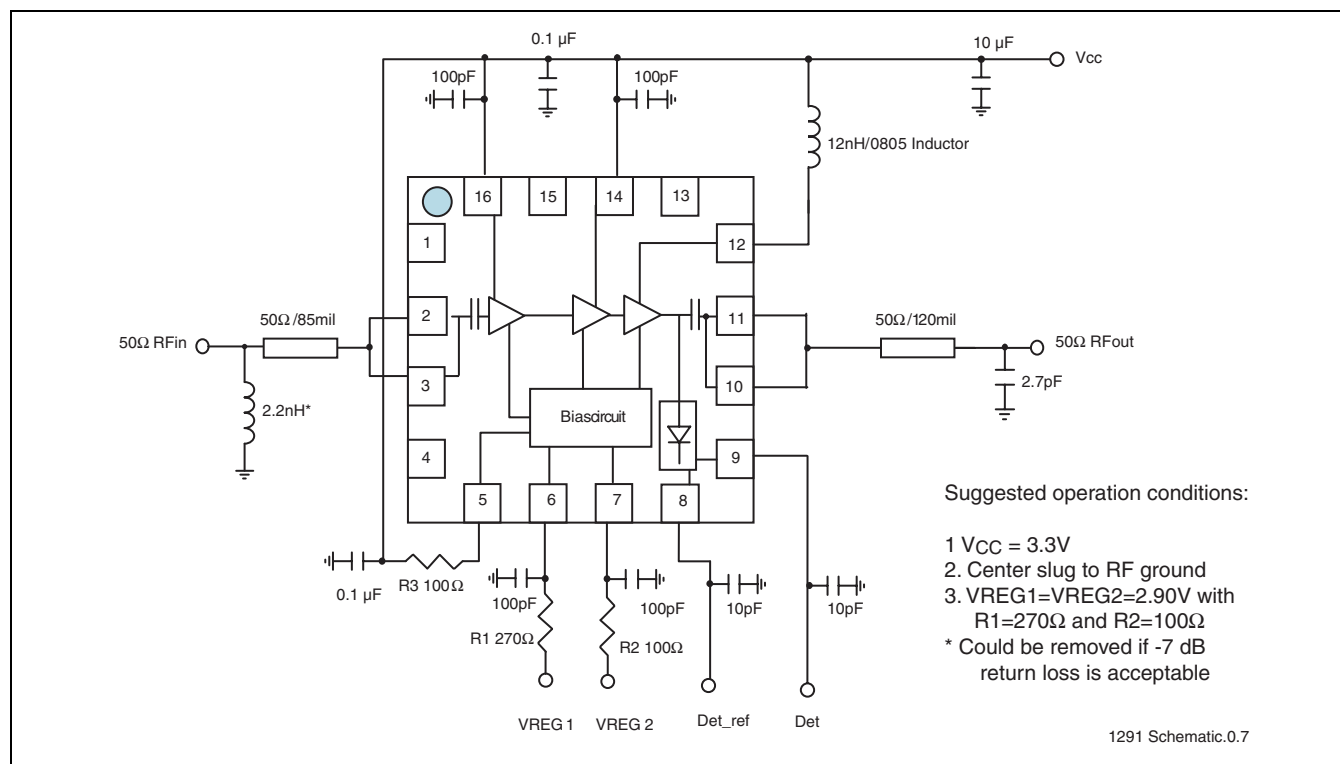


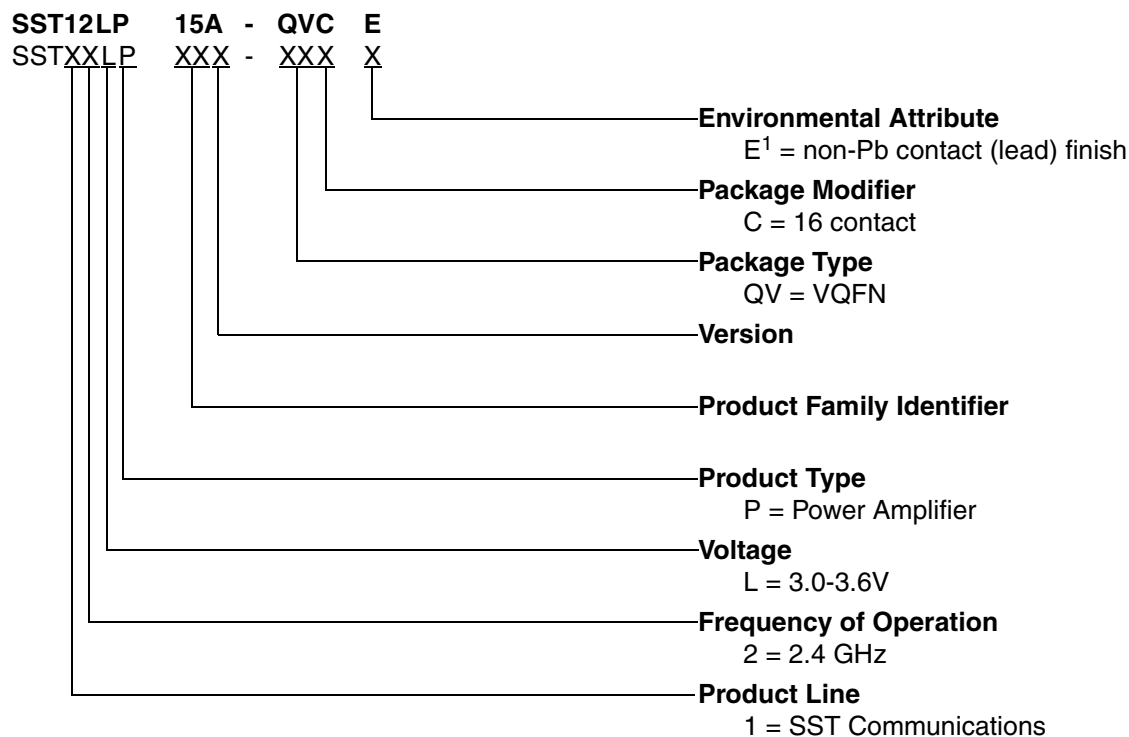
FIGURE 11: Typical Schematic for High-Power, High-Efficiency 802.11b/g Applications



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### PRODUCT ORDERING INFORMATION



1. Environmental suffix "E" denotes non-Pb solder.  
SST non-Pb solder devices are "RoHS Compliant".

### Valid combinations for SST12LP15A

SST12LP15A-QVCE

### SST12LP15A Evaluation Kits

SST12LP15A-QVCE-K

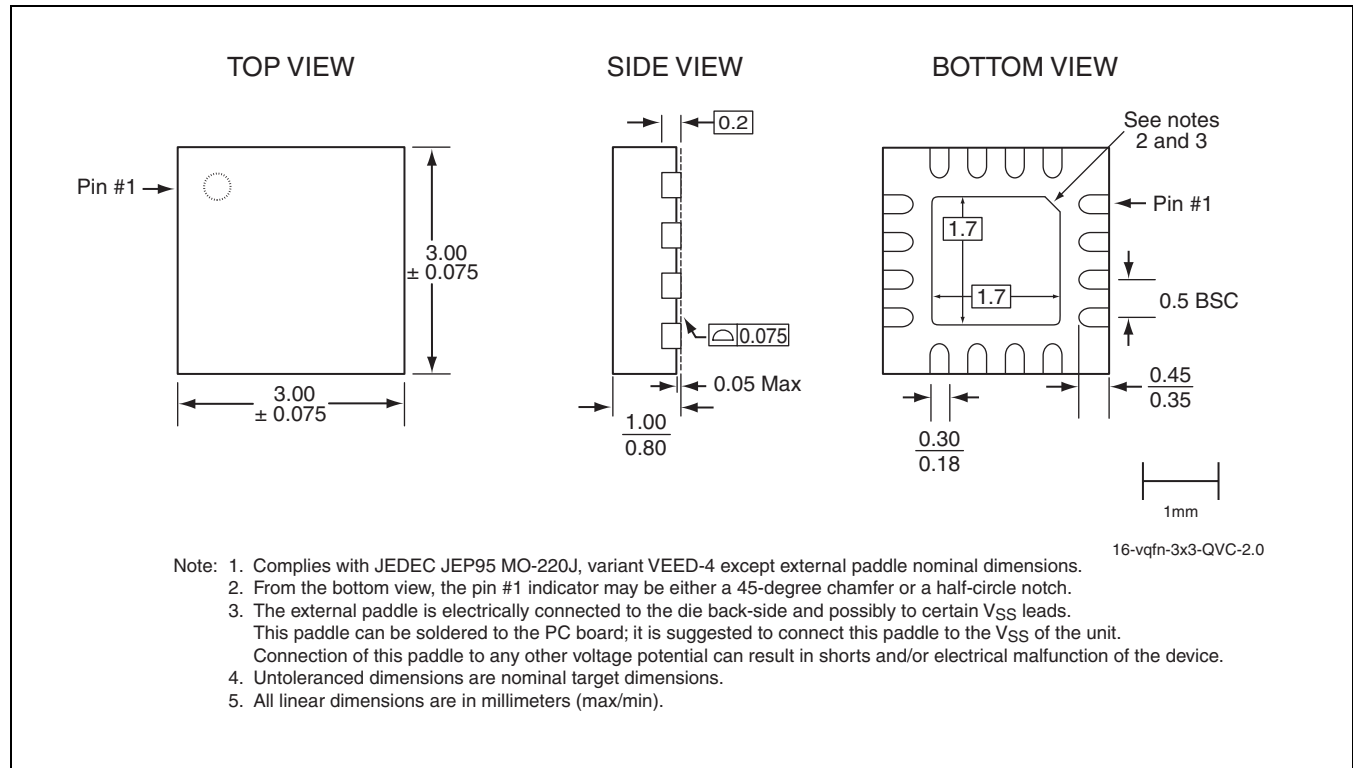
**Note:** Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.



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### PACKAGING DIAGRAMS



**FIGURE 12: 16-contact Very-thin Quad Flat No-lead (VQFN)  
SST Package Code: QVC**

**TABLE 4: Revision History**

Revision	Description	Date
00	• Initial release of data sheet	Mar 2005
01	• Updated values for gain and efficiency on page 1 • Updated values for VREG1 and VREG2 in Table 2 on page 4 • Removed stability parameter from Table 3 on page 5 • Updated the typical application schematic on page 10 • Updated QVC package drawing. • Updated “Absolute Maximum Stress Ratings” on page 4	Mar 2006
02	• Added information for 2.3-2.4 and 2.5-2.6 applications • Removed leaded part numbers	Jul 2006
03	• Updated “Features:” and “Product Description” on page 1 • Revised Table 2 on page 4 and Table 3 on page 5 • Updated values in Figure 11 on page 10. • Removed two schematics • Updated Figures 3 - 8	Sep 2008
04	• Updated “Contact Information” on page 13.	Feb 2009

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